S8550

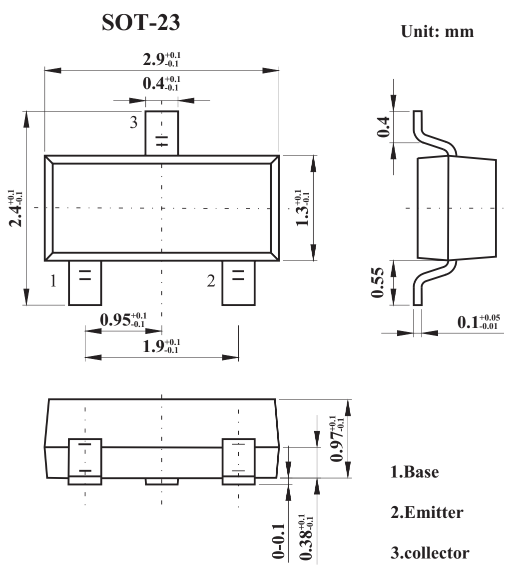
SOT-23 Plastic-Encapsulate Transistors

Features

- ●Collector current: IC-=0.5A
- ●Weight:0.080 grams(approx)
- ●PNP Transistors

MECHANICAL DATA

- ●Case style:SOT-23molded plastic
- ●Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

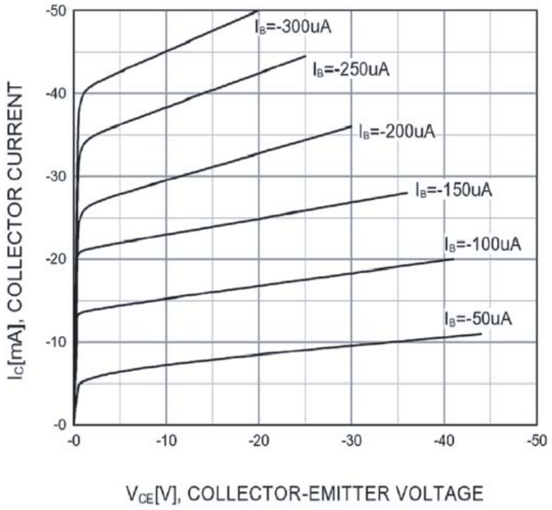
Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=-100μA, I_E=0	-40			V
Collector-emitter breakdown voltage	V_{CEO}	I_C=-1mA, I_B=0	-25			V
Emitter-base breakdown voltage	V_{EBO}	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V, I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-20V, I_B=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-1V, I_C=-50mA	200		350	
		V_{CE}=-1V, I_C=-500mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=-50mA			-1.2	V
Transition frequency	f_T	V_{CE}= -6V, I_C= -20mA,f=30MHz	150			MHz

■ Marking

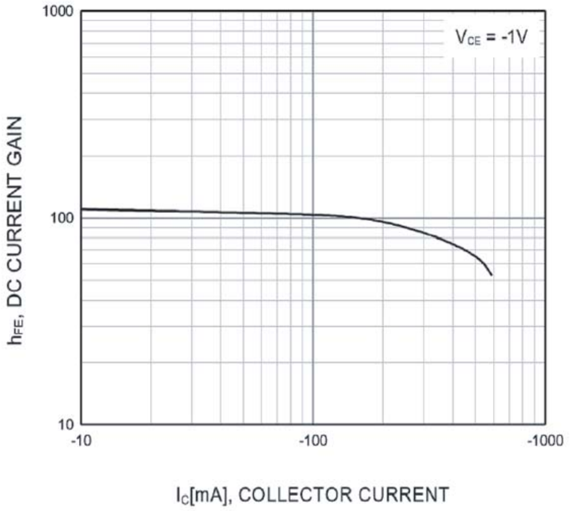
Marking	2TY

RATINGS AND CHARACTERISTIC CURVES

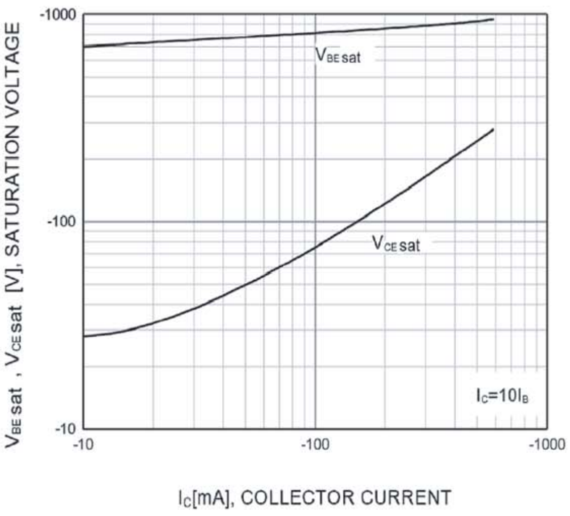
■ Typical Characteristics



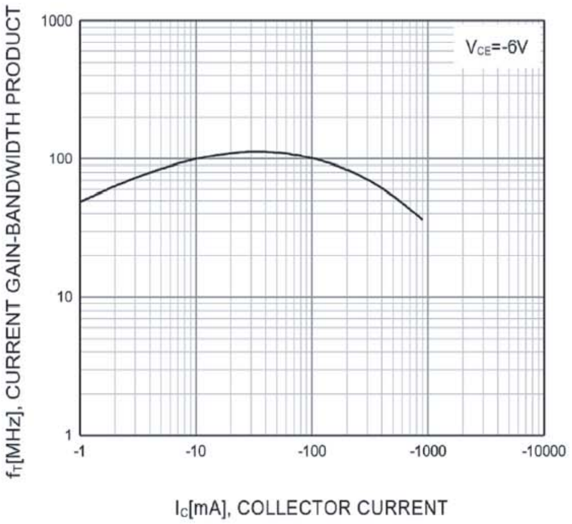
Static Characteristic



DC current Gain



Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product